

3DD100, 3DD101, 3DD102**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97 for all, QZJ840611A, QZJ840611 for 3DD100 and 3DD101.
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP for all, JT, JCT, GS, G, G+ for 3DD100 and 3DD101.

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD100		3DD101		3DD102
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	100	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	100	150	200	250	300
Emitter-Base Voltage	V_{EBO}	V	4		4	4	
Max. Collector Current	I_{CM}	A	1.5		5	5	
Max. Collector Dissipation	P_{CM}	W	20 ($T_c \leq 75^\circ C$)		50 ($T_c \leq 75^\circ C$)		
Junction Temperature	T_{jm}	$^\circ C$	175				
Storage Temperature	T_{stg}	$^\circ C$	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	0.2 ($V_{CE}=50V$)		1.0 ($V_{CE}=50V$)		
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.0 ($I_C=1A, I_B=0.1A$)		A~C: 0.8, D~E: 1.5 ($I_C=2.5A, I_B=0.25A$)		
DC Current Gain	h_{FE}		Max.:120,Min.:20 ($V_{CE}=5V, I_C=0.5A$)		Max.:120, Min.:20 ($V_{CE}=5V, I_C=2A$)		
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 4 ($I_E=1mA$)		≥ 4 ($I_E=1mA$)		

h_{FE} Colored:

Color	Brown	Red	Orange
h_{FE}	20~40	40~80	80~120

Outline and Dimensions: